CORA Cork Open Research Archive
Cartlann Taighde Oscailte Chorcaí

Title	Resonance assisted jump-in voltage reduction for electrostatically actuated nanobeam-based gateless NEM switches.
Authors	Meija, Raimonds;Livshits, Alexander I.;Kosmaca, Jelena;Jasulaneca, Liga;Andzane, Jana;Biswas, Subhajit;Holmes, Justin D.;Erts, Donats
Publication date	2019-07-08
Original Citation	Meija, R., Livshits, A. I., Kosmaca, J., Jasulaneca, L., Andzane, J., Biswas, S., Holmes, J. D. and Erts, D. (2019) 'Resonance assisted jump-in voltage reduction for electrostatically actuated nanobeam-based gateless NEM switches', Nanotechnology, 30(38), 385203 (6 pp). doi: 10.1088/1361-6528/ab2b11
Type of publication	Article (peer-reviewed)
Link to publisher's version	https://iopscience.iop.org/article/10.1088/1361-6528/ab2b11 - 10.1088/1361-6528/ab2b11
Rights	© 2019 IOP Publishing Ltd. This is an author-created, un-copyedited version of an article accepted for publication in Nanotechnology The publisher is not responsible for any errors or omissions in this version of the manuscript or any version derived from it. The Version of Record is available online at https://doi.org/10.1088/1361-6528/ab2b11. As the Version of Record of this article has been published on a subscription basis, this Accepted Manuscript will be available for reuse under a CC BY-NC-ND 3.0 licence after a 12 month embargo period. - https://creativecommons.org/licences/by-nc-nd/3.0
Download date	2026-11-06 09:13:43
Item downloaded from	https://hdl.handle.net/10468/8213



University College Cork, Ireland
Coláiste na hOllscoile Corcaigh

Supplementary information

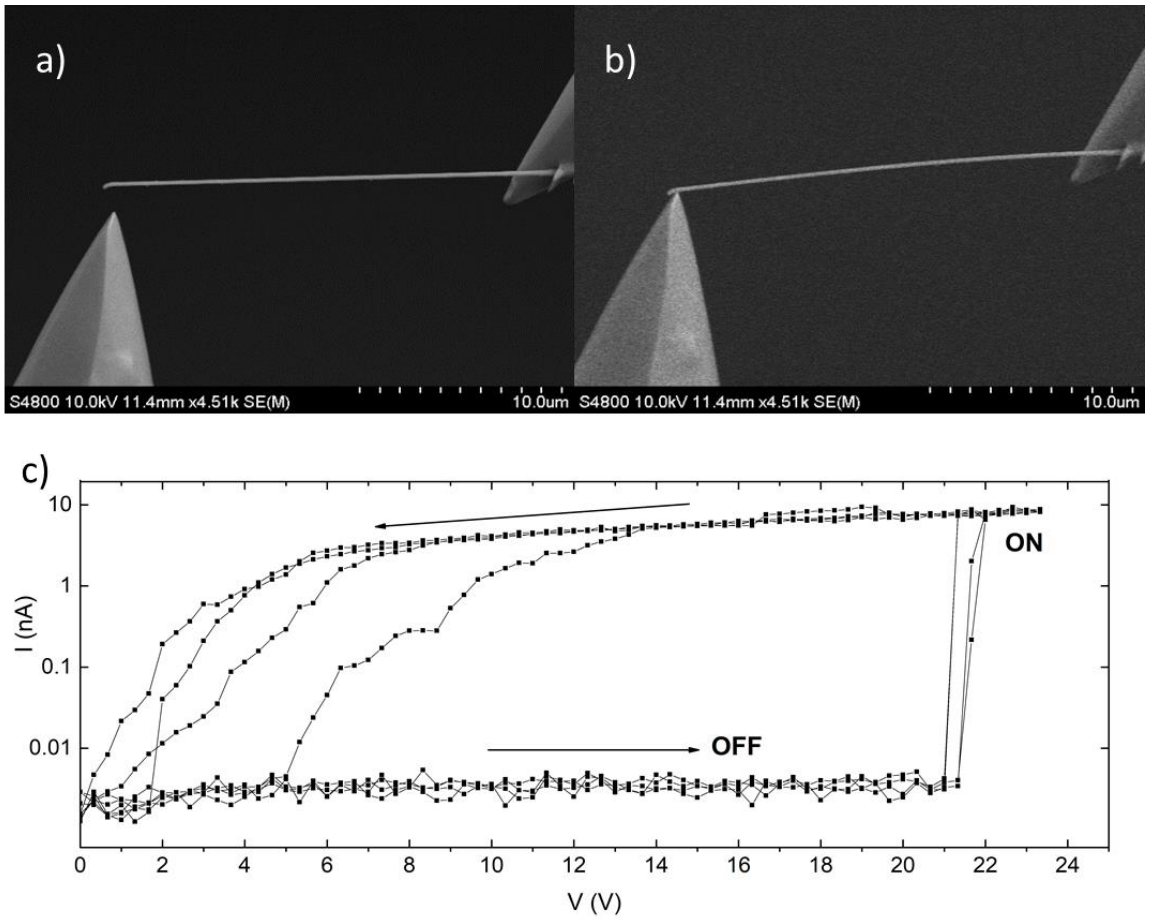


Figure 1. Additional NEM device with repeated measurements for GeSn nanowire with L = 22 µm, d = 125 nm. a) – nanowire in an OFF state; b) – nanowire in ON state, c) – repeated IV measurements of NEM device. The AC assisted jump in occurred at 5 V + 0.6 V DC + AC voltage.